PNP/NPN Epitaxial Planar Silicon Transistors



2SB1454/2SD2202

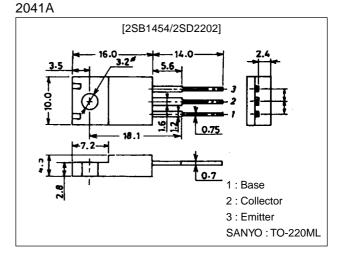
# **High-Current Switching Applications**

## **Features**

- · Low collector-to-emitter saturation voltage.
- · Large current capacity.
- · Micaless package facilitating easy mounting.

## Package Dimensions

unit:mm



():2SB1454

# **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(–)90	V
Collector-to-Emitter Voltage	VCEO		(–)80	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		()6	V
Collector Current	ι <sub>C</sub>		(–)5	A
Collector Current (Pulse)	ICP		()9	A
Collector Dissipation	PC		2.0	W
		Tc=25°C	25	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### **Electrical Characteristics at Ta = 25°C**

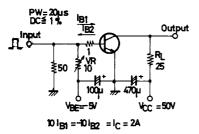
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =(-)80V, I <sub>E</sub> =0			(–)0.1	mA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(–)0.1	mA
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)1A	70*		280*	
	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)3A	30			
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)1A		20		MHz
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)3A, I <sub>B</sub> =(-)0.3A			0.4	V
					(-0.5)	V
* : The 2SB1454/2SD2202 are classified by 1.	A h <sub>FE</sub> as follow	s: 70 Q 140 100 R 200 140 S 2	280			

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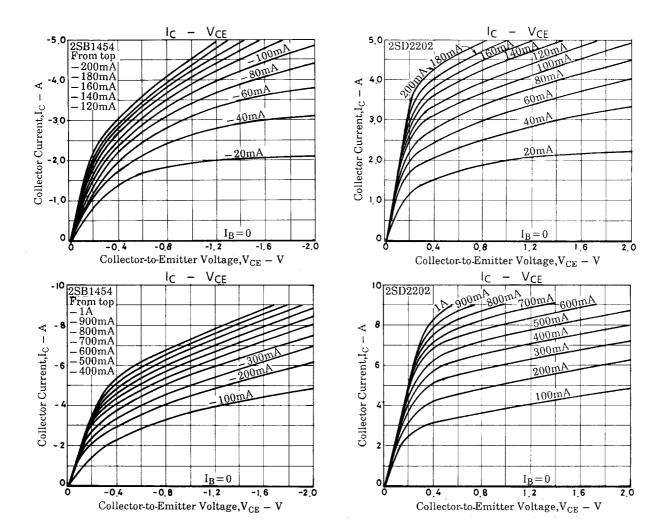
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	
Collector-to-Base Breakdown Voltage	V <sub>(BR)</sub> CBO	I <sub>C</sub> =(-)1mA, I <sub>E</sub> =0	(–)90			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(−)1mA, R <sub>BE</sub> =∞	(–)80			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =(-)1mA, I <sub>C</sub> =0	(–)6			V
Turn-ON Time	ton	See specified test circuit.		(0.2)		μs
				0.1		μs
Storage Time	tstg	See specified test circuit.		(0.7)		μs
				1.2		μs
Fall Time	t <sub>f</sub>	See specified test circuit.		(0.2)		μs
				0.4		μs

#### **Switching Time Test Circuit**

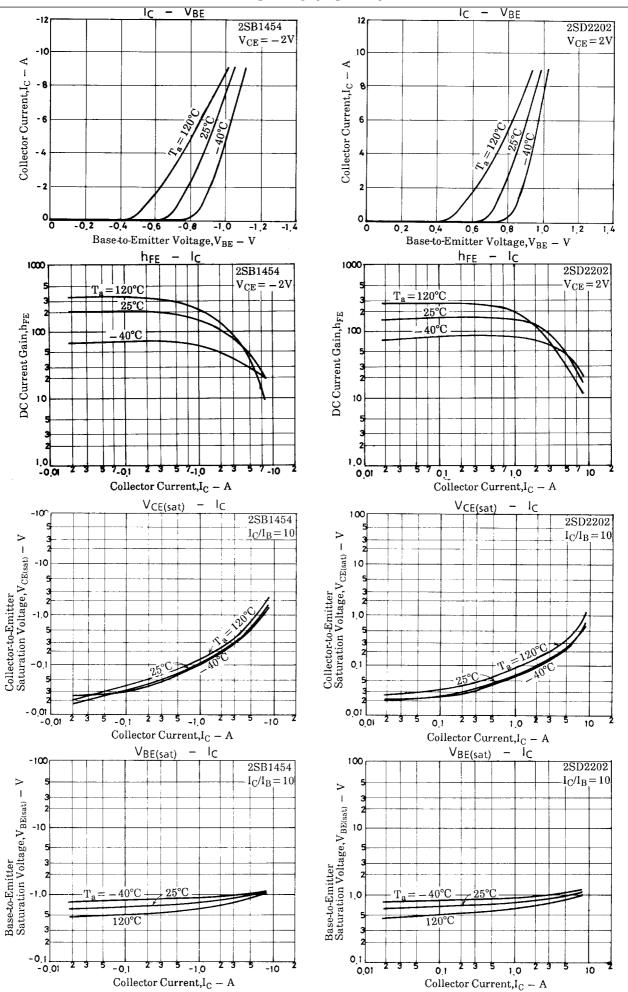


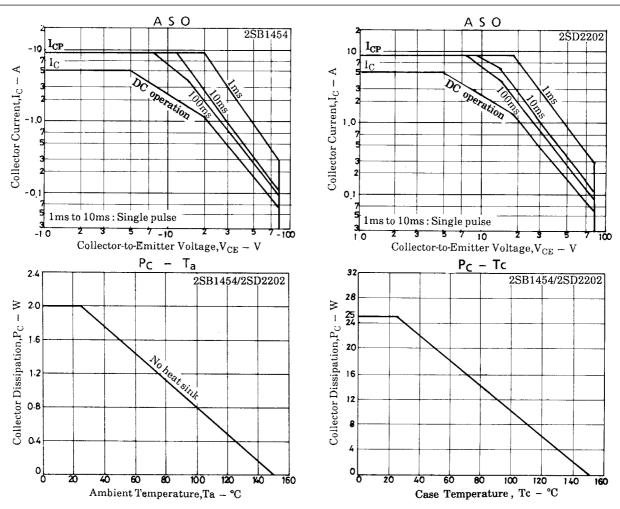
For PNP, the polarity is reversed.

Unit (resistance :  $\Omega$ , capacitance : F)



### 2SB1454/2SD2202





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